

Marcos H Degani

List of Publications by Year in descending order

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docs citations

45

times ranked

325

citing authors

#	ARTICLE	IF	CITATIONS
1	Exciton binding energy in quantum-well wires. Physical Review B, 1987, 35, 9345-9348.	3.2	130
2	Electron energy levels in a Γ -doped layer in GaAs. Physical Review B, 1991, 44, 5580-5584.	3.2	84
3	Bound impurity in GaAs-Ga $_{1-x}$ Al $_x$ As quantum-well wires. Physical Review B, 1988, 37, 1402-1405.	3.2	74
4	Polaron effects in one-dimensional lateral quantum wires and parabolic quantum dots. Physical Review B, 1990, 42, 11950-11952.	3.2	66
5	Electron-phonon interaction effects in a quasi-two-dimensional electron gas in the GaAs-Ga $_{1-x}$ Al $_x$ As heterostructure. Physical Review B, 1987, 35, 7717-7720.	3.2	47
6	Numerical Calculations of the Quantum States in Semiconductor Nanostructures. Journal of Computational and Theoretical Nanoscience, 2010, 7, 454-473.	0.4	46
7	Polaron effects on excitons in GaAs-Ga $_{1-x}$ Al $_x$ As quantum wells. Physical Review B, 1987, 35, 4507-4510.	3.2	42
8	Stark ladders in strongly coupled GaAs-AlAs superlattices. Applied Physics Letters, 1991, 59, 57-59.	3.3	37
9	Electron-interface-phonon interaction in GaAs/AlAs and InAs/GaSb heterojunctions. Surface Science, 1988, 196, 459-465.	1.9	32
10	Bound polaron in GaAs-GaAlAs quantum-well structures. Physical Review B, 1986, 33, 4090-4093.	3.2	29
11	Polaron effects on the impurity binding energy in quantum wires. Physical Review B, 1995, 52, 4662-4665.	3.2	25
12	Exciton binding energy in type-II heterojunctions. Physical Review B, 1990, 42, 11701-11707.	3.2	20
13	Many-polaron interaction effects in GaAs-GaAlAs quantum-well-wires. Solid State Communications, 1991, 79, 473-476.	1.9	19
14	Single-electron states and conductance in lateral-surface superlattices. Physical Review B, 1991, 44, 10901-10904.	3.2	19
15	Competition between interface and bulk phonons in GaAs/AlAs and InAs/GaSb quantum wells. Superlattices and Microstructures, 1989, 5, 141-144.	3.1	18
16	Competition between shallow-impurity and T-shaped quantum-wire states. Physical Review B, 2002, 66, .	3.2	16
17	Theory of bound polarons near interfaces of polar semiconductors. Physical Review B, 1991, 43, 4113-4118.	3.2	15
18	Two-dimensional magnetoexcitons in type-II semiconductor quantum dots. Physical Review B, 2008, 78, .	3.2	15

#	ARTICLE	IF	CITATIONS
19	Modification of the Electron-Phonon Interactions in GaAs-GaAlAs Heterojunctions. Physical Review Letters, 1987, 59, 2820-2820.	7.8	13
20	Cyclotron mass of electrons in GaAs-Ga _{1-x} Al _x As quantum wells. Physical Review B, 1988, 38, 8477-8479.	3.2	13
21	Magnetoexciton electroabsorption in T-shaped semiconductor quantum wires. Physical Review B, 2002, 66, .	3.2	13
22	Resonances of trion states in quantum dot molecules tuned by an electric field. Physical Review B, 2007, 75, .	3.2	13
23	Photocurrent Calculation of Intersubband Transitions to Continuum-Localized States in GaAs/AlGaAs Multiquantum Wells for Mid-Infrared Photodetector. IEEE Journal of Quantum Electronics, 2013, 49, 747-752.	1.9	13
24	Exploring Parity Anomaly for Dual Peak Infrared Photodetection. IEEE Journal of Quantum Electronics, 2016, 52, 1-6.	1.9	12
25	Dynamical mass effect on confined exciton states. Physical Review B, 1988, 38, 8533-8536.	3.2	11
26	Dynamics of excitons and Coulomb beats in a quantum dot molecule. Applied Physics Letters, 2006, 89, 152109.	3.3	10
27	Energy-momentum relation for polarons in quantum-well wires. Physical Review B, 1989, 40, 11937-11939.	3.2	9
28	Anisotropic polarons near interfaces of polar semiconductors. Physical Review B, 1990, 41, 3572-3577.	3.2	9
29	Intersubband optic phonon resonances in electrostatically confined quantum wires. Applied Physics Letters, 1993, 62, 2824-2826.	3.3	9
30	Nonlinear optical absorption of semiconductor quantum wires: Photoexcitation dynamical effects. Physical Review B, 2003, 68, .	3.2	9
31	Multiple-photon peak generation near the $\approx 10 \text{ } \mu\text{m}$ range in quantum dot infrared photodetectors. Journal of Applied Physics, 2011, 109, 064510.	2.5	9
32	Infrared photocurrent with one- and two-photon absorptions in a double-barrier quantum well system. Journal of Applied Physics, 2011, 110, .	2.5	9
33	Electron-phonon effects on the ground impurity level in quasi-one-dimensional semiconductor heterostructures. Superlattices and Microstructures, 1989, 6, 111-113.	3.1	7
34	Temperature dependence of the polaron mass in a GaAs _{1-x} Al _x As quantum well wire. Superlattices and Microstructures, 1989, 5, 137-139.	3.1	7
35	Optimal control of universal quantum gates in a double quantum dot. Physical Review B, 2018, 97, .	3.2	7
36	Cyclotron resonance of electrons in GaAs _{1-x} Al _x As heterojunctions. Superlattices and Microstructures, 1989, 6, 107-110.	3.1	6

#	ARTICLE	IF	CITATIONS
37	Electron-polar optical phonon scattering rates in multisubband quantum wire structures. <i>Surface Science</i> , 1990, 229, 279-281.	1.9	6
38	Ground-state energy of the polaron gas in two-dimensional semiconductor microstructures. <i>Physical Review B</i> , 1988, 37, 10137-10142.	3.2	5
39	Coherent population trapping in intersubband photocurrent spectra. <i>Physical Review B</i> , 2011, 83, .	3.2	5
40	Exceptionally Narrow-Band Quantum Dot Infrared Photodetector. <i>IEEE Journal of Quantum Electronics</i> , 2012, 48, 1360-1366.	1.9	4
41	Exciton spin precessions in a biased double quantum dot. <i>Applied Physics Letters</i> , 2006, 88, 162108.	3.3	3
42	Generation and control of spin-polarized photocurrents in GaMnAs heterostructures. <i>Applied Physics Letters</i> , 2014, 104, 022105.	3.3	3
43	Negative photoconductance in a biased multiquantum well with filter barriers. <i>Physical Review B</i> , 2014, 89, .	3.2	2
44	Generation of spin polarized currents with coherent trapping in magnetic semiconductors. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 135105.	2.8	1
45	Subband mixing inducing negative resistance. <i>Solid State Communications</i> , 1993, 86, 301-304.	1.9	0